30H15K/D

N-Channel Enhancement Mode Power MOSFET

30V, 150A

$R_{DS(ON)}$<3.4mΩ @ V_{GS} =10V

$R_{DS(ON)}$<6.5mΩ @ V_{GS} =4.5V

试用水印 试用水印 试用水印

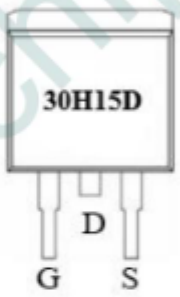
Features

- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Package



TO-252 (30H15K)



TO-263 (30H15D)

试用水印 试用水印 试用水印

Absolute Maximum Ratings (T_C=25℃unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	150	A
		T_C = 100℃	98	A
I_{DM}	Pulsed Drain Current		430	A
E_{AS}	Single Pulsed Avalanche Energy		225	mJ
P_D	Power Dissipation	T_C = 25℃	108	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.4	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

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